

BYC60W-1200P

Hyperfast power diode

Product data sheet

Rev.02 - 18 May 2023

1. General description

EEPP[™]- Efficiency Enhanced Pt Planar diode in a 2-leads TO247-2L plastic package.

2. Features and benefits

- · Fast switching
- Reduces switching losses with improved lower reverse recovery charge
- Soft recovery characteristics
- Low thermal resistance
- Low leakage current
- High operating temperature capability (T_{j (max)} = 175°C)
- Higher I_{FSM} capability
- Planar termination structure

3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			1200			V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 80 °C; Fig. 1; Fig. 2; Fig. 3	60			A	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 80 °C; square-wave pulse	120		A		
I_{FSM}	non-repetitive peak forward current	$t_{\rm p}$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>	500 550			A	
		$t_{\rm p}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse;			А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.8	3.3	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>		-	2.2	-	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	- 55 -		ns		
Avalanch	ie energy						
E _{AS}	non-repetitive avalanche energy	T _{j(init)} = 25 °C		50	-	-	mJ

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode		К <u> </u> А 001aaa020
mb	mb	mounting base; connected to cathod	T0247-2L	

6. Ordering information

Table 3. Ordering information

Т	ype number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
B	3YC60W-1200P	TO247-2L	BYC60W-1200PQ	Tube	30	TO247P-2L	31-Mar-2023

7. Marking

Table 4. Marking codes

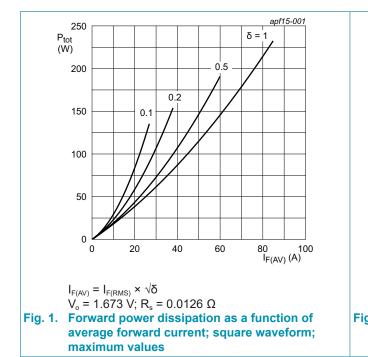
Type number	Marking codes
BYC60W-1200P	BYC60W 1200P

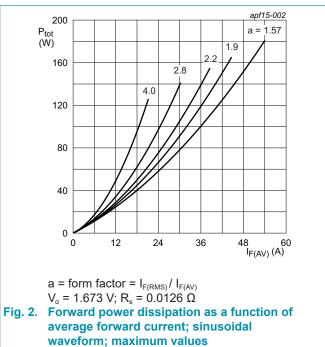
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

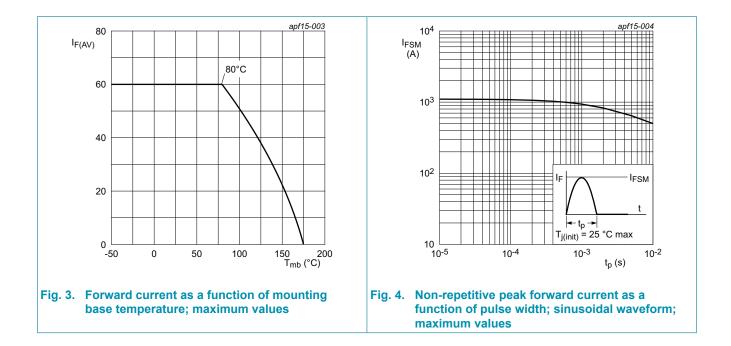
Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		1200	V
V_{RWM}	crest working reverse voltage		1200	V
V _R	reverse voltage	DC	1200	V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 80 °C; Fig. 1; Fig. 2; Fig. 3	60	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 80 °C; square-wave pulse	120	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	500	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	550	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C





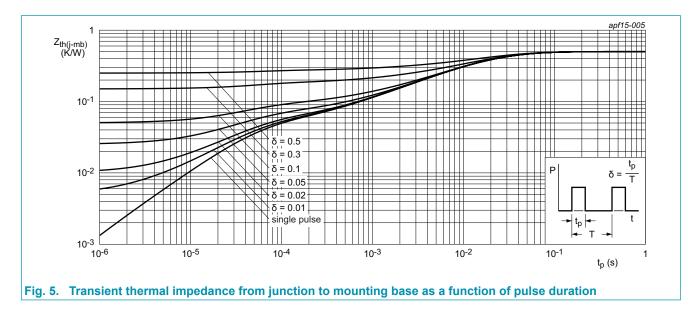
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9. Thermal characteris	tics
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Table 6. Th	ermal characteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th}(j\text{-}mb)}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

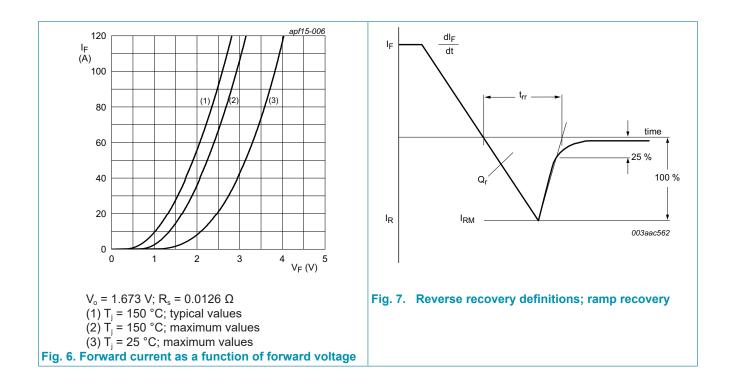


10. Characteristics

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
Static ch	aracteristics		· · · ·			
V _F	forward voltage	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.8	3.3	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>	-	2.2	-	V
I _R	reverse current	V _R = 1200 V; T _j = 25 °C	-	-	250	μA
		V _R = 1200 V; T _j = 150 °C	-	-	2	mA
Dynamic	characteristics	1	I			
Q _r	reverse charge	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	952	-	nC
		$ I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; T_j = 125 ^\circ\text{C}; \text{ Fig. 7} $	-	2920	-	nC
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 150 ^\circ\text{C}; \text{ Fig. 7}$	-	3425	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	55	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	96	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	194	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 150 ^\circ\text{C}; \text{ Fig. 7}$	-	212	-	ns
I _{RM}	peak reverse recovery current	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	20	-	A
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	30.2	-	А
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	32.3	-	A
Avalanch	e energy	· · · · · · · · · · · · · · · · · · ·				
E _{AS}	non-repetitive avalanche energy	T _{j(init)} = 25 °C	50	-	-	mJ

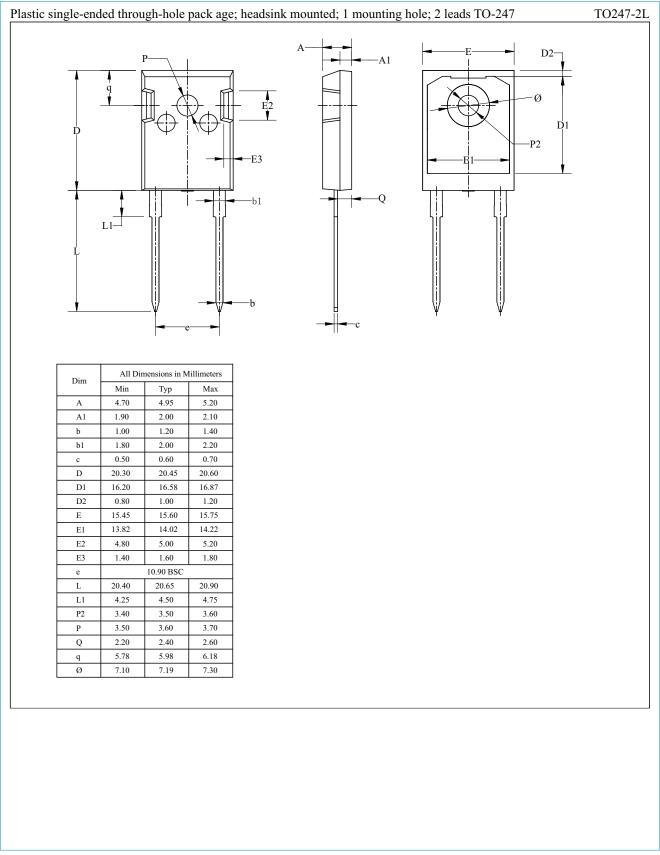
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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- The term 'short data sheet' is explained in section "Definitions". [2]
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